

MOSFET Theory (H.2)

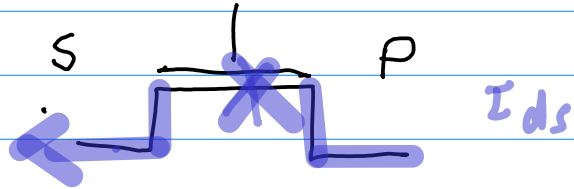
20160227

nMOS Operation Modes
Bias Method

Copyright (c) 2015 Young W. Lim.

Permission is granted to copy, distribute and/or modify this document under the terms of the GNU Free Documentation License, Version 1.2 or any later version published by the Free Software Foundation; with no Invariant Sections, no Front-Cover Texts, and no Back-Cover Texts. A copy of the license is included in the section entitled "GNU Free Documentation License".

Cut Off

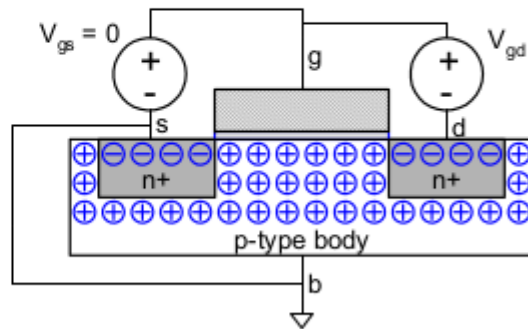


☐ No channel

☐ $I_{ds} \approx 0$

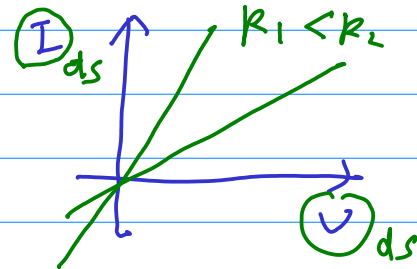
Cut off

$$\underline{V_{gs} < V_t}$$



Linear

Linear Region

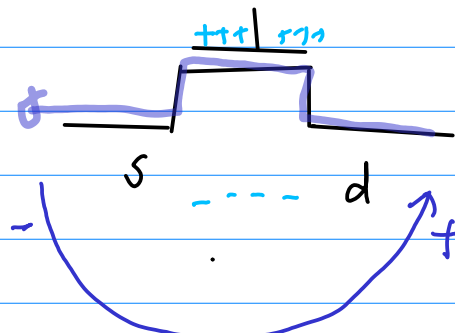
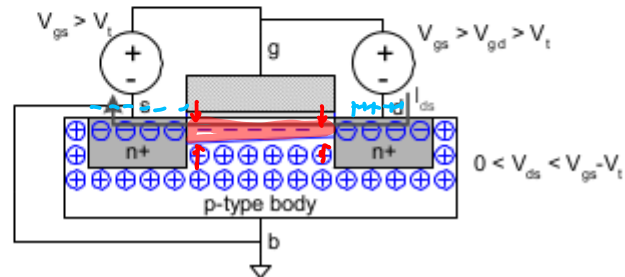
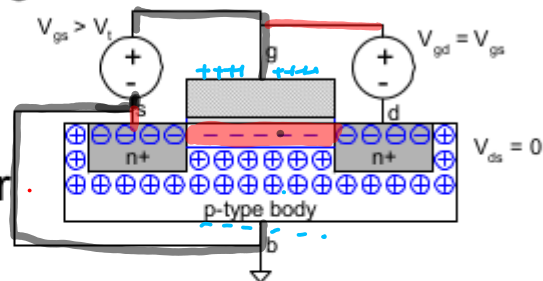


$$R = \frac{V}{I}$$

$$\frac{1}{R} = \frac{I}{V}$$

$$V_g > V_t$$

- Channel forms $\rightarrow$ current flows
- Current flows from d to s
 - e^- from s to d
- I_{ds} increases with V_{ds}
- Similar to linear resistor



$$0 < V_{ds} < V_{gs} - V_t$$

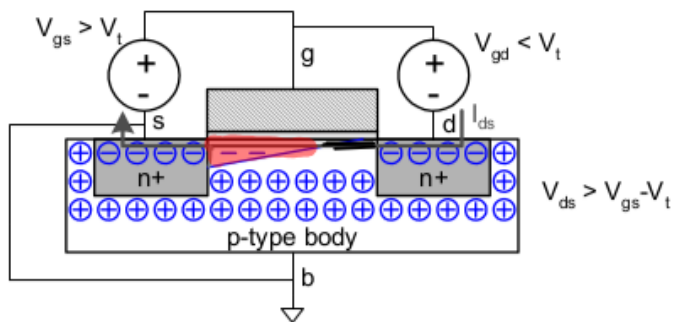
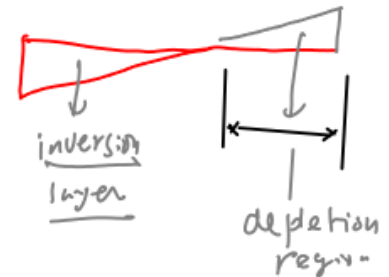
channel
at (D)

$$V_g > V_t$$

inversion
layer (channel
at (S))

nMOS Saturation

- ❑ Channel pinches off
- ❑ I_{ds} independent of V_{ds}
- ❑ We say current saturates
- ❑ Similar to current source



Bias Conditions

$V_{GS} < V_t$ • Cut off

$V_{GS} > V_t$ • Linear
• Saturation

$V_{GS} > V_t \rightarrow$ S-side channel

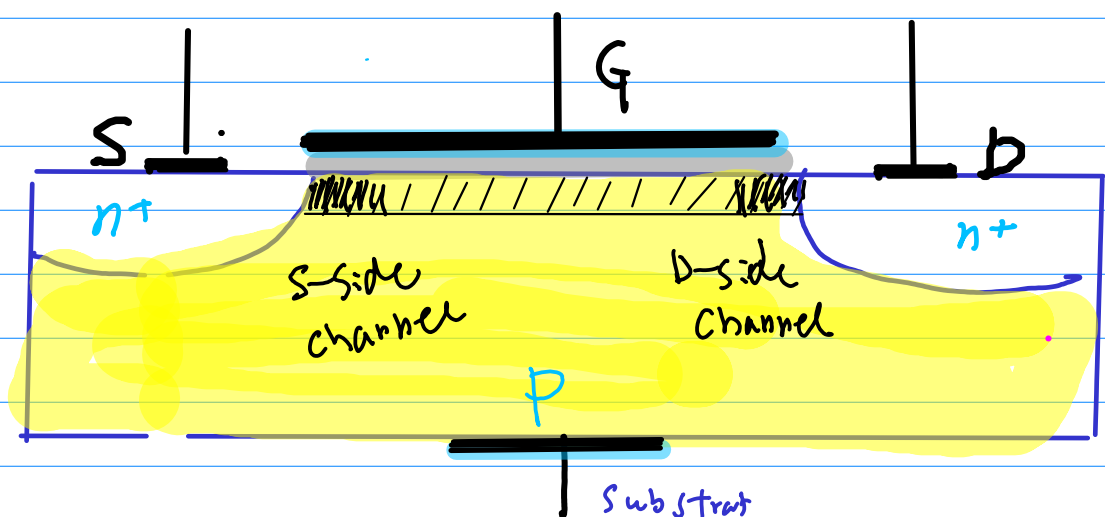
$V_{GD} > V_t \rightarrow$ D-side channel

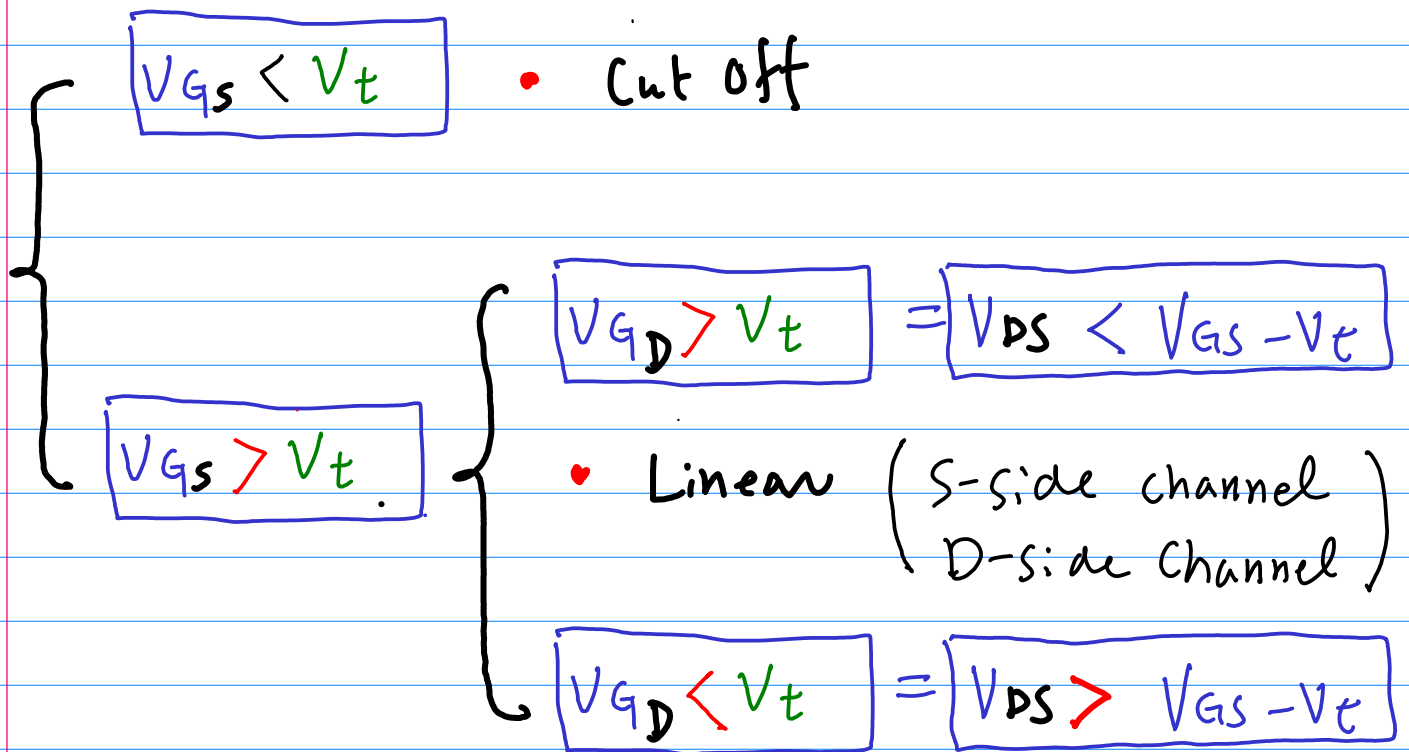
$$V_{DS} < V_{GS} - V_t$$

$$V_{GD} = V_{GS} - V_{DS} > V_t$$

$$V_{GS} - V_t > V_{DS}$$

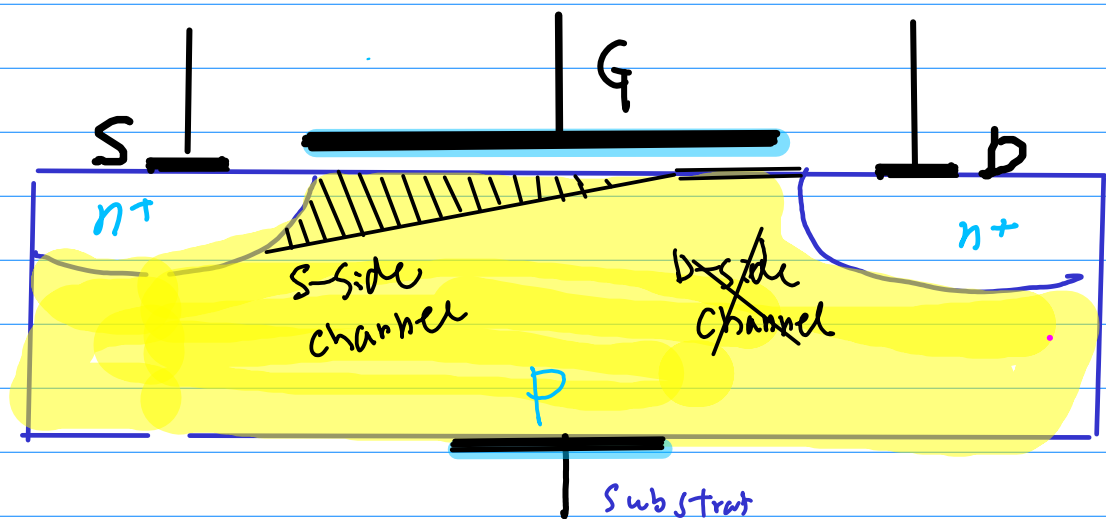
LINEAR





• Saturation (S-side channel
~~D-side Channel~~)

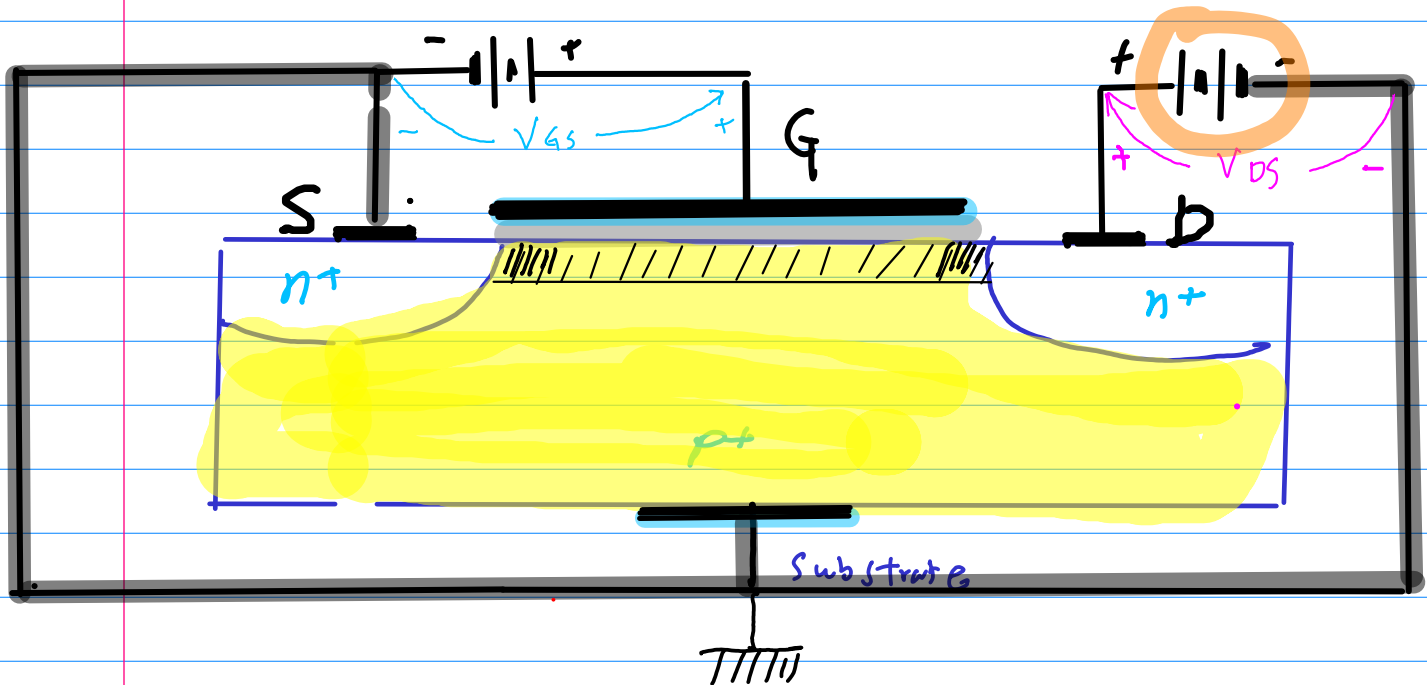
SATURATION



LINEAR

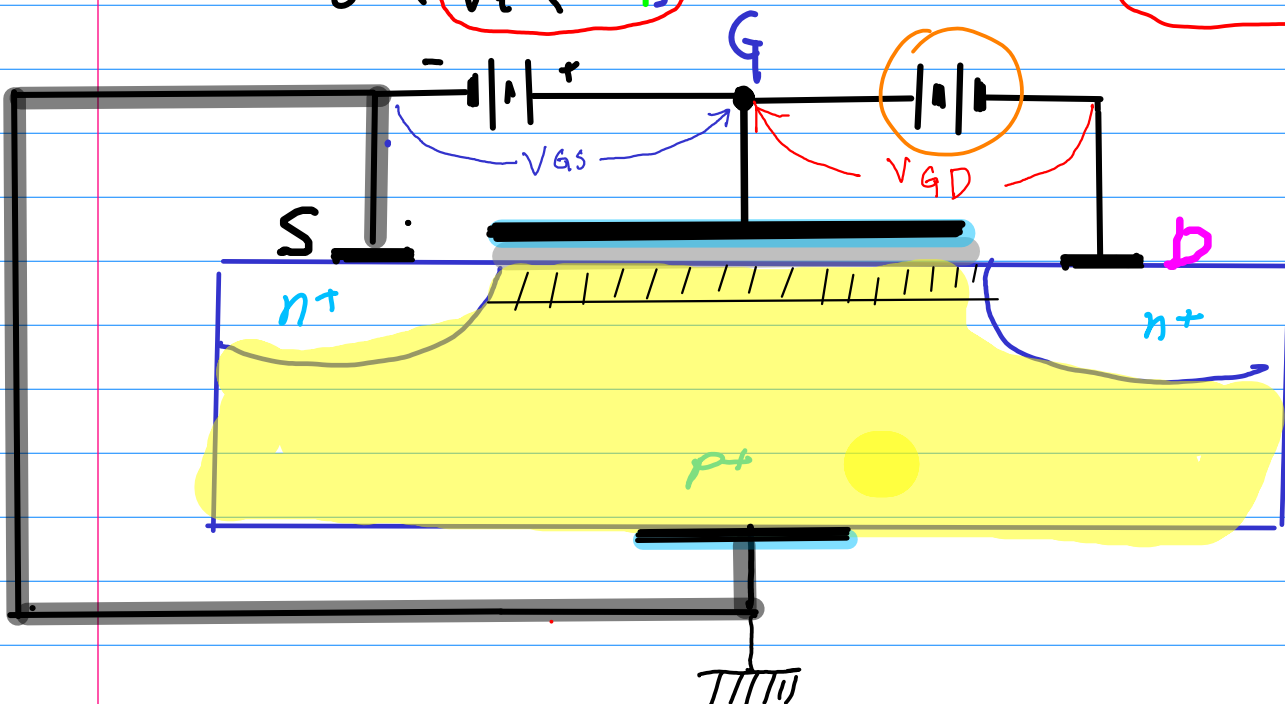
$$0 < V_t < V_{GS}$$

$$0 < V_{ps} < V_{G_s} - V_T$$

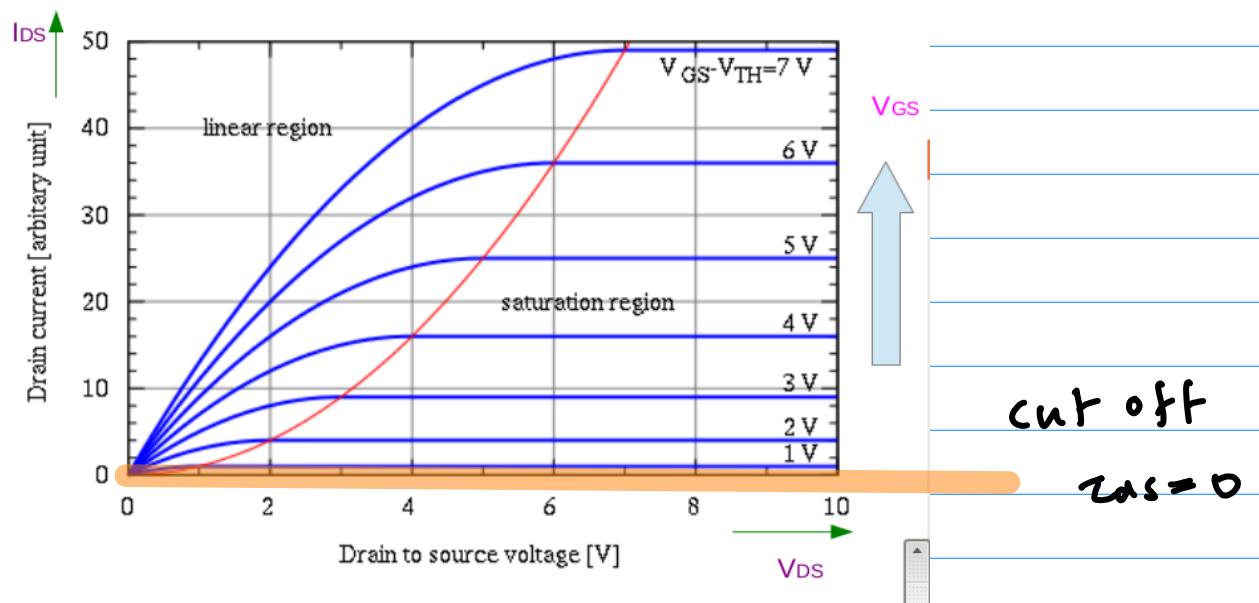
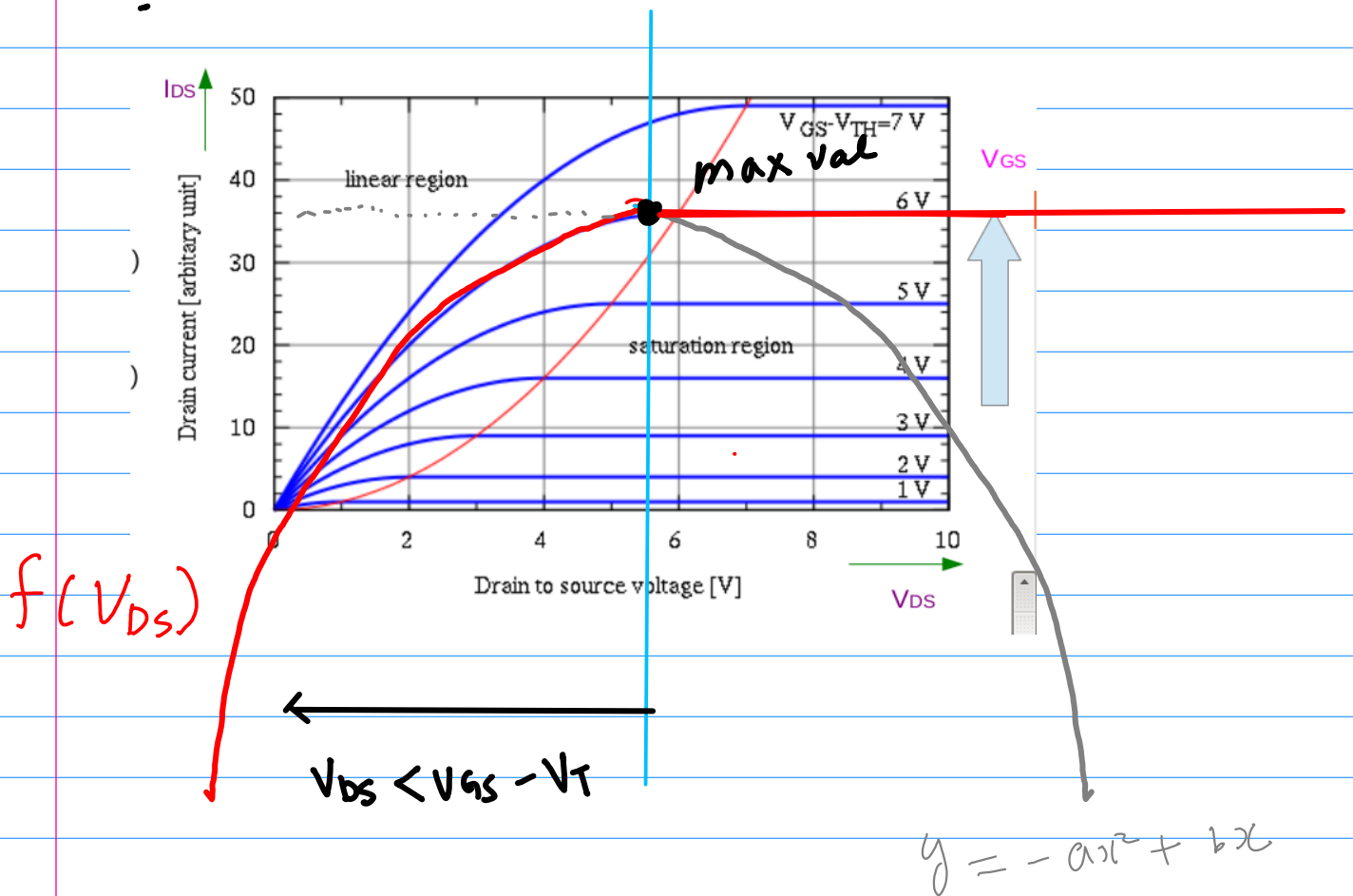


$$0 < V_t < V_{GS}$$

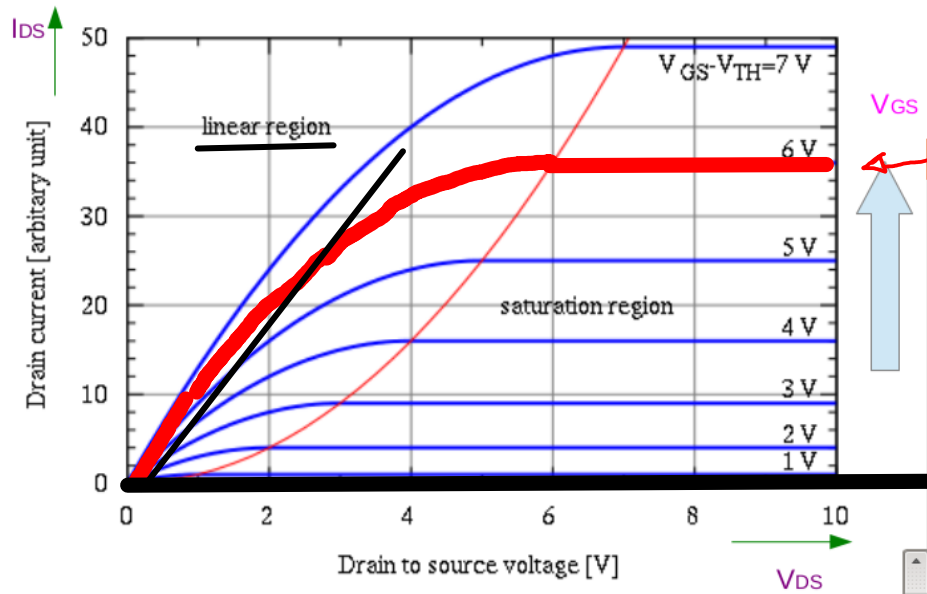
$$0 < V_t < V_{GD}$$



Linear $\rightarrow$ left side of a quadratic eq



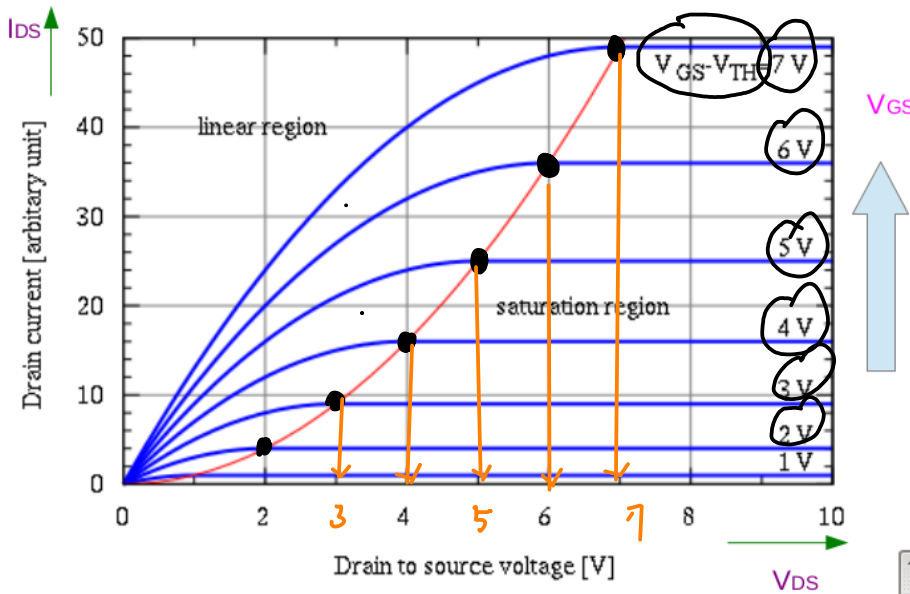
a given V_{GS}



$$V_{GS} - V_T \leq 0$$

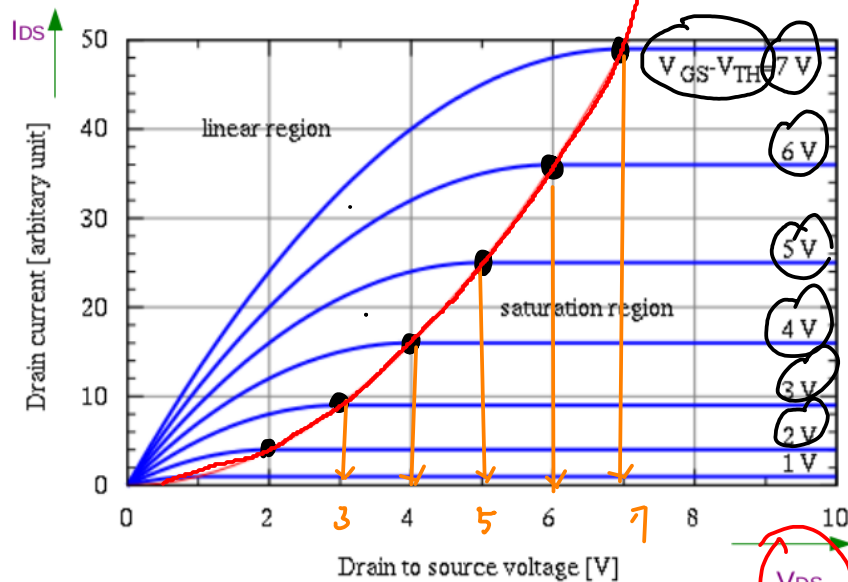
$$V_{GS} \leq V_T$$

Cut off



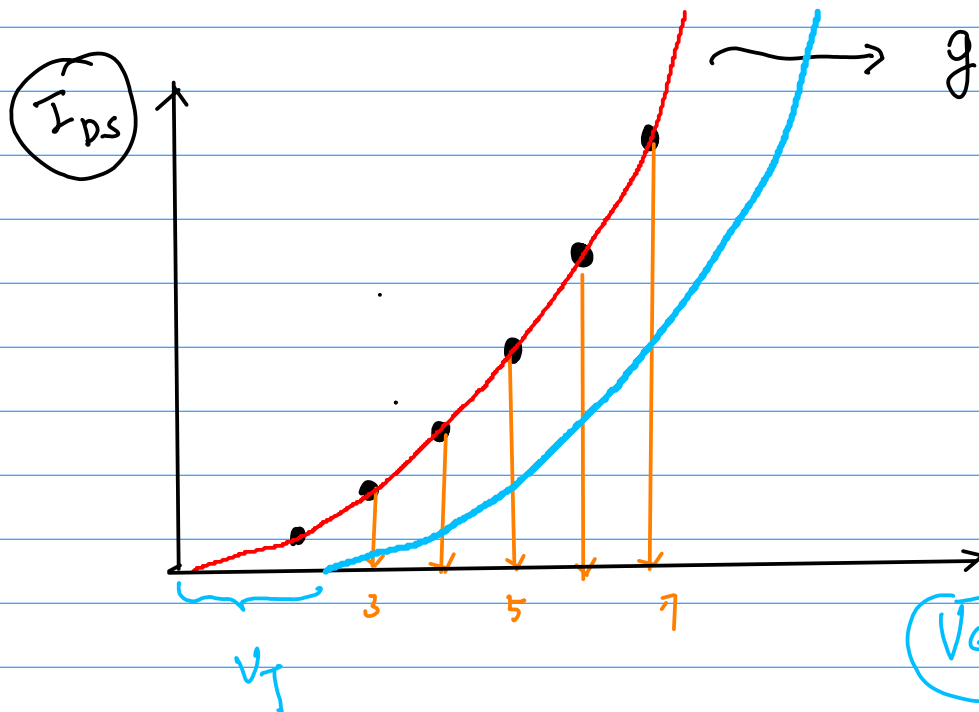
$$V_{GS} - V_T = V_{DS}$$

7	7
6	6
5	5
4	4
3	3
2	2
1	1



points where
 $V_{DS} = V_{GS} - V_T$

$$f(V_{DS}) = f(V_{GS} - V_T)$$



$$g(V_{GS} - V_T)$$

↓

$$g(V_{GS})$$

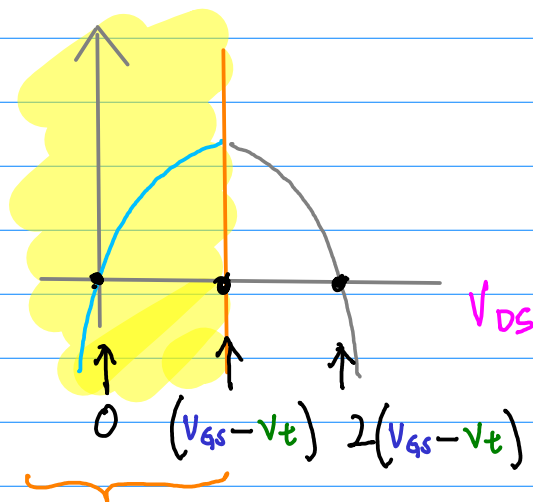
$$g(V_T) = 0$$

$$f(V_{GS} - V_T) = \frac{\mu}{2} (V_{GS} - V_T)^2 = g(V_{GS})$$

$$I_{ds} = \begin{cases} 0 & V_{gs} < V_t & \text{cutoff} \\ \beta \left(V_{gs} - V_t - \frac{V_{ds}}{2} \right) V_{ds} & V_{ds} < V_{dsat} & \text{linear} \\ \frac{\beta}{2} (V_{gs} - V_t)^2 & V_{ds} > V_{dsat} & \text{saturation} \end{cases}$$

for a given V_{gs}

$$\begin{aligned} f(V_{ds}) &= \frac{\beta}{2} \left(2(V_{gs} - V_t) - V_{ds} \right) V_{ds} \\ &= \frac{\beta}{2} \left(2(V_{gs} - V_t) V_{ds} - V_{ds}^2 \right) \end{aligned}$$



$$\begin{aligned} y &= (2a - x)x \\ &= (2ax - x^2) \end{aligned}$$

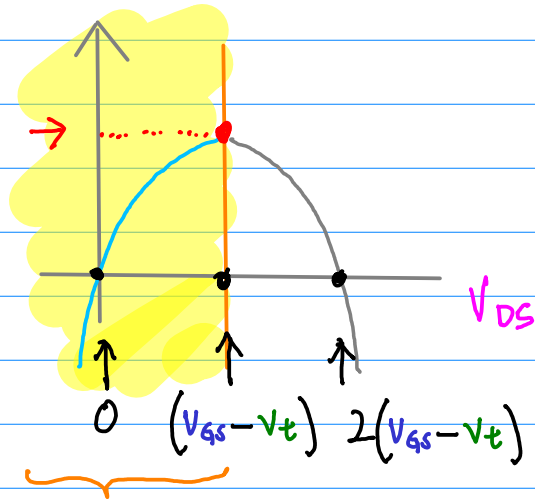
$x = 0, 2a$ roots
sym axis
 $x = a$

$$V_{ds} \leq V_{gs} - V_t$$

Linear Eq & Max value

for a given V_{GS} const

$$f(V_{DS}) = \frac{\theta}{2} \left(2(V_{GS} - V_t) - V_{DS} \right) V_{DS}$$

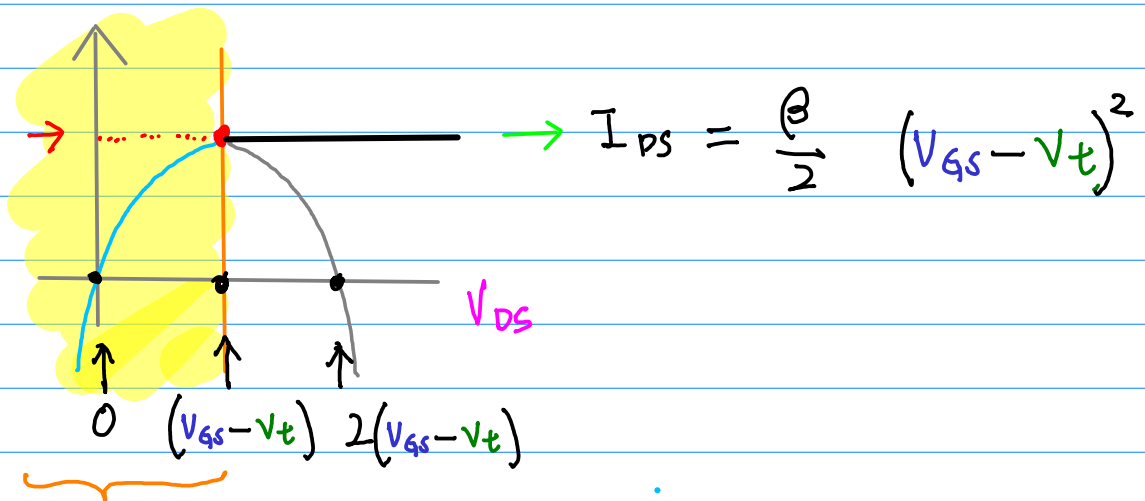


$$V_{DS} \leq V_{GS} - V_t$$

$$\begin{aligned} f(V_{GS} - V_t) &= \frac{\theta}{2} \left(2(V_{GS} - V_t) - (V_{GS} - V_t) \right) (V_{GS} - V_t) \\ &= \frac{\theta}{2} (V_{GS} - V_t)^2 \end{aligned}$$

$$I_{DS} = \frac{\theta}{2} (V_{GS} - V_t)^2 \quad : \text{Saturated current}$$

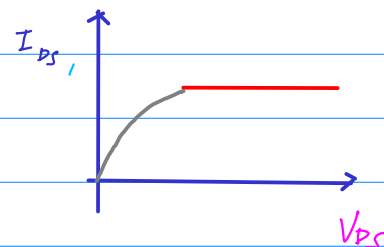
Saturation



$$V_{DS} \leq V_{GS} - V_t$$

* for a given V_{GS} (const with respect to V_{DS})

$$f(V_{DS}) = \frac{\beta}{2} (V_{GS} - V_t)^2 = \text{constant}$$

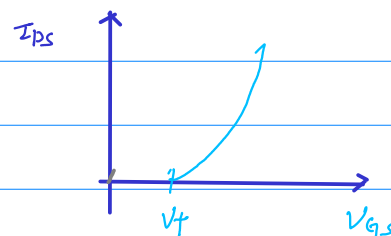


* But a function of V_{GS}

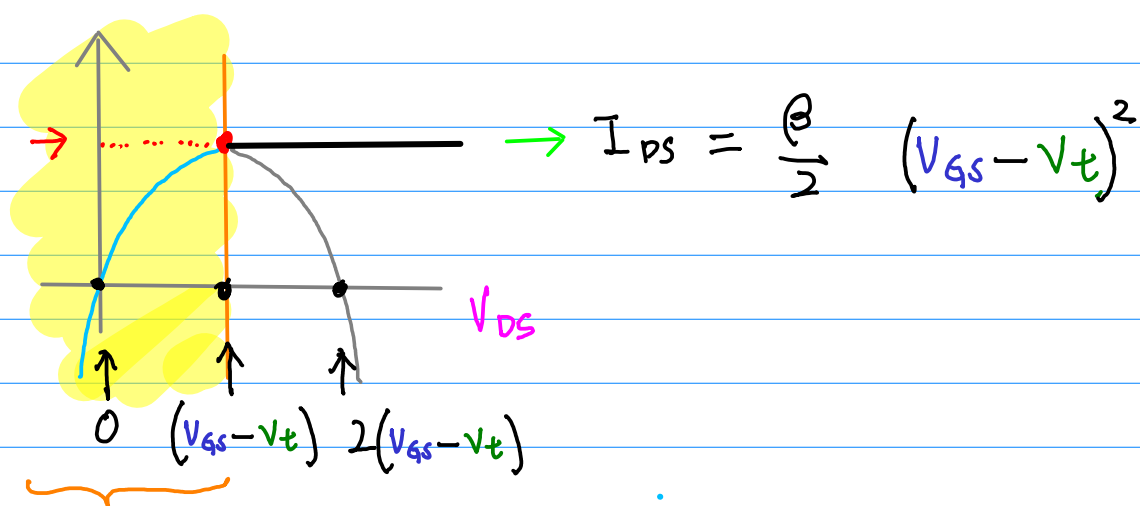
$$g(V_{GS}) = \frac{\beta}{2} (V_{GS} - V_t)^2$$

now V_{GS} is
an independent
variable

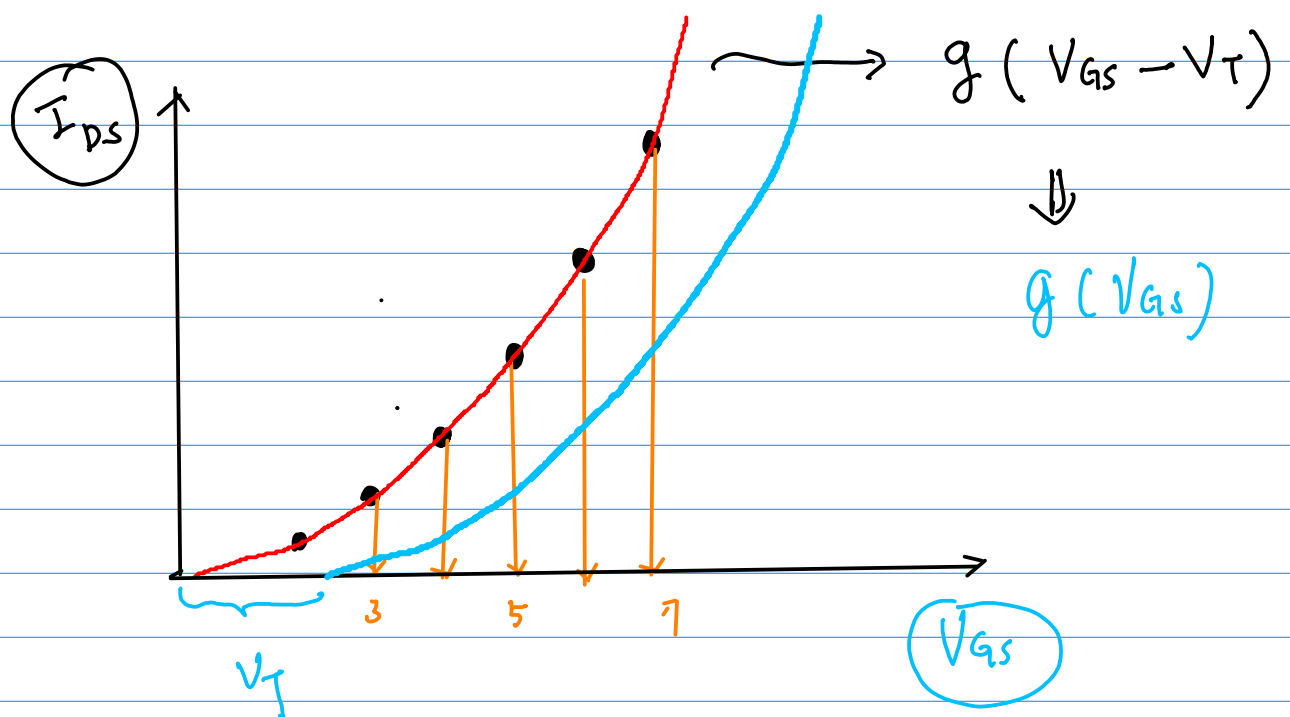
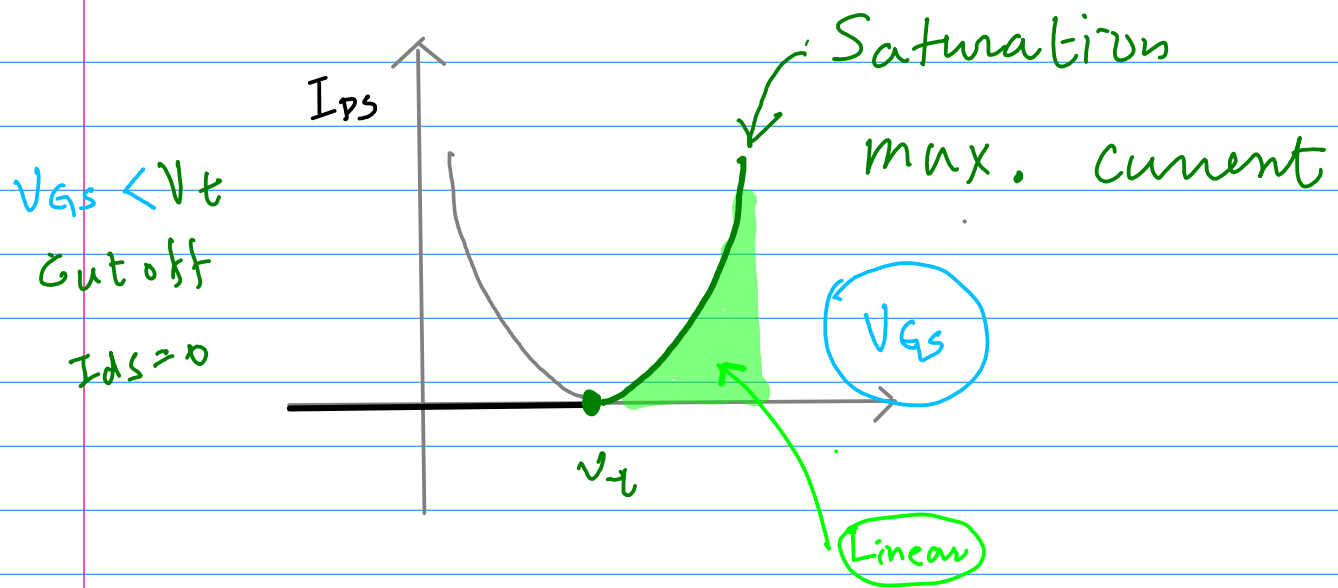
Quadratic equation of V_{GS}



$$I_{ds} = \begin{cases} 0 & V_{gs} < V_t & \text{cutoff} \\ \beta \left(V_{gs} - \cancel{V_t} - \frac{V_{ds}}{2} \right) V_{ds} & V_{ds} < V_{dsat} & \text{linear} \\ \frac{\beta}{2} \left(V_{gs} - \cancel{V_t} \right)^2 & V_{ds} > V_{dsat} & \text{saturation} \end{cases}$$



$$V_{DS} \leq V_{GS} - V_t$$



① Cut off

$$V_{GS} < V_t$$

② Linear

S  D

$$0 < V_t < V_{GS}$$

S  D

$$0 < V_t < V_{GD}$$

$\equiv$

$$0 < V_t < V_{GS}$$

$$V_{DS} < V_{GS} - V_t$$

$$V_{GD} = V_{GS} - V_{DS} > V_t$$

$$V_{GS} - V_t > V_{DS}$$

③ Saturation

S  D

$$0 < V_t < V_{GS}$$

S  D

$$V_{GD} < V_t$$

$\equiv$

$$0 < V_t < V_{GS}$$

$$V_{GS} - V_t < V_{DS}$$

① Cut off $V_{GS} < V_t$

$$I_{DS} = 0$$

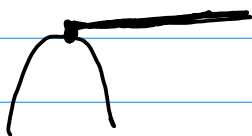
② Linear $0 < V_t < V_{GS}$ $V_{DS} < V_{GS} - V_t$

$$I_{DS} = f(V_{DS}) = \frac{\beta}{2} \left(2(V_{GS} - V_t) - V_{DS} \right) V_{DS}$$
$$= \frac{\beta}{2} \left(2(V_{GS} - V_t) V_{DS} - V_{DS}^2 \right)$$



③ Saturation $0 < V_t < V_{GS}$ $V_{GS} - V_t < V_{DS}$

$$I_{DS} = f(V_{DS}) = \frac{\beta}{2} (V_{GS} - V_t)^2 = \text{constant!}$$



* for a given V_{GS}

$$V_{DS} = V_{GS} - V_{GD} = \cancel{V_G} - V_S - (\cancel{V_G} - V_D) \\ = V_D - V_S$$

$$V_{GD} = V_{GS} - V_{DS}$$

$$V_{GD} \geq V_t \quad \underline{\text{Linear}}$$

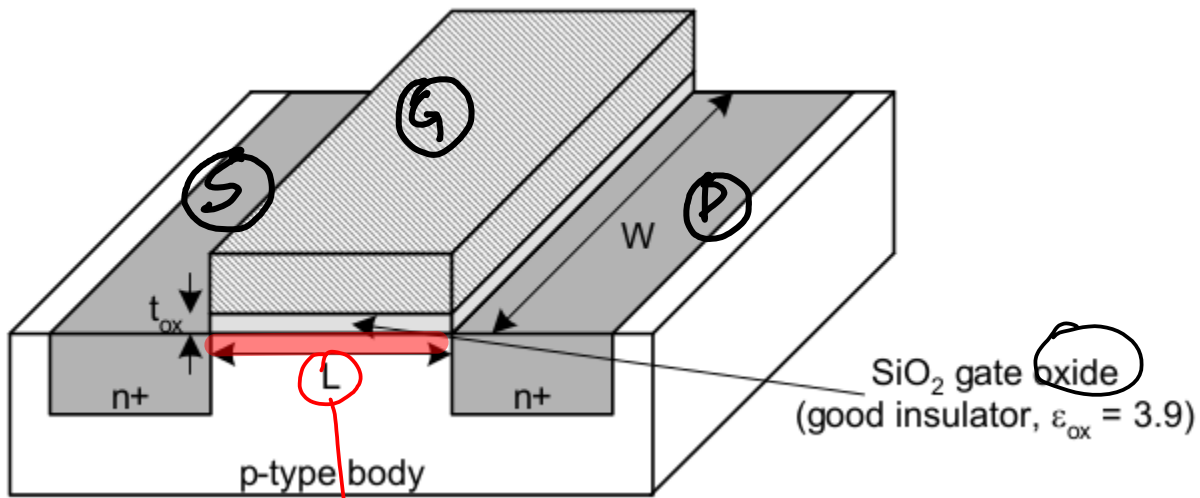
$$V_{GS} - V_{DS} \geq V_t$$

$$V_{GD} < V_t \quad \underline{\text{Saturation}}$$

$$V_{GS} - V_{DS} < V_t$$

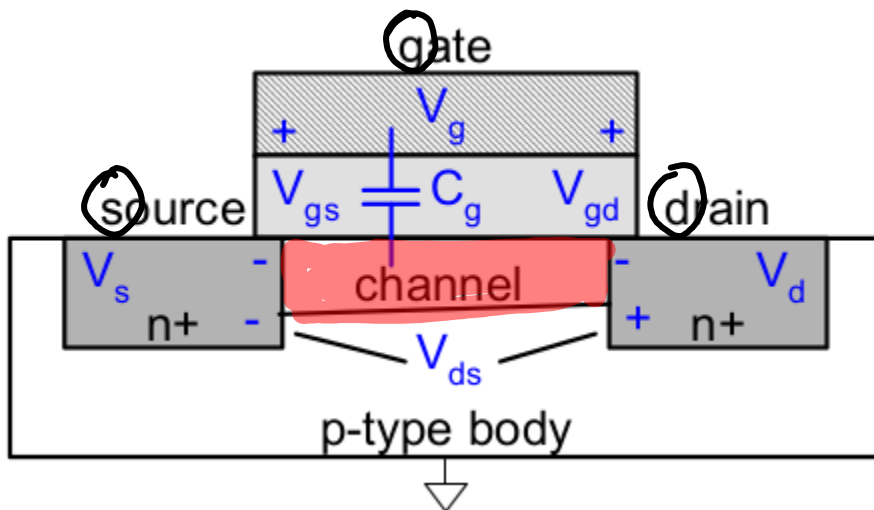
Transconductance

$$\beta = \frac{1}{R}$$



channel Length

$L \uparrow \quad I_{ds} \downarrow$
 $W \uparrow \quad I_{ds} \uparrow$



$\frac{W}{L} \uparrow \quad I_{ds} \uparrow$

$$\beta = \mu_n C_{ox} \left(\frac{W}{L} \right)$$

① Cut off $V_{GS} < V_t$

$$I_{DS} = 0$$

② Linear

$$0 < V_t < V_{GS} \quad V_{DS} < V_{GS} - V_t$$

$$I_{DS} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right) \left(2(V_{GS} - V_t) - V_{DS} \right) V_{DS}$$

$$= \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right) \left(2(V_{GS} - V_t) V_{DS} - V_{DS}^2 \right)$$

β

③ Saturation

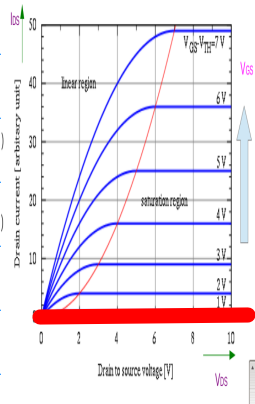
$$0 < V_t < V_{GS} \quad V_{GS} - V_t < V_{DS}$$

β

$$I_{DS} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right) (V_{GS} - V_t)^2 = \text{constant!}$$

* for a given V_{GS}

① Cut off

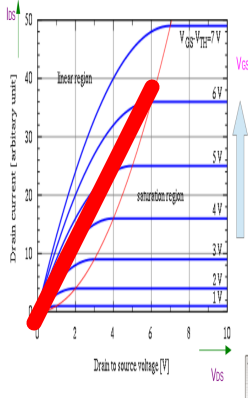


OFF

$$\text{slope} = \frac{1}{R} = 0$$

$$R = \infty$$

② Linear



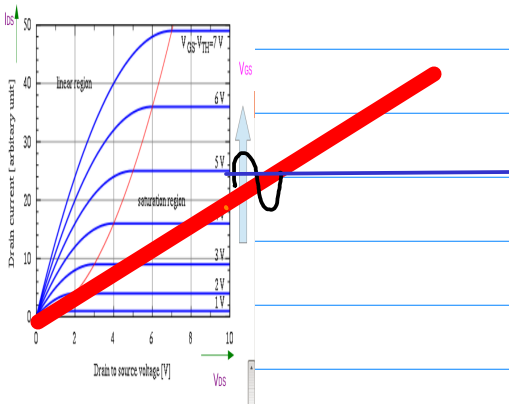
ON

$$\text{slope} = \frac{1}{R}$$

$$0 < R < \infty$$

Digital

③ Saturation



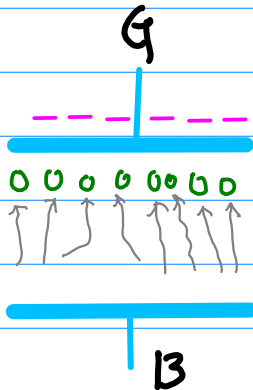
AMP

Analog

MOS structure : V_{GB} Bias

Accumulation

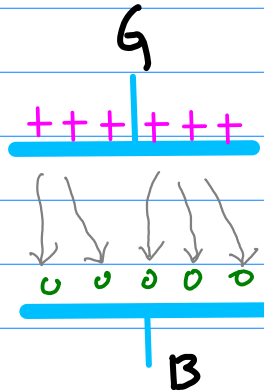
majority carriers



attracts
holes

Depletion

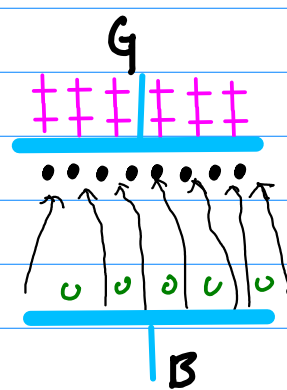
majority carrier



repels
holes

Inversion

minority carrier



repels holes
attracts electrons

$$V_{GB} < 0$$

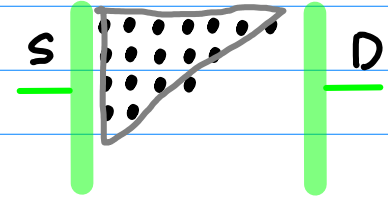
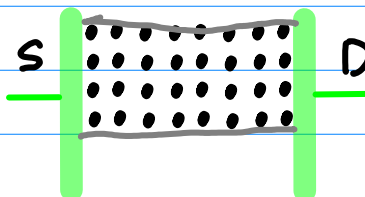
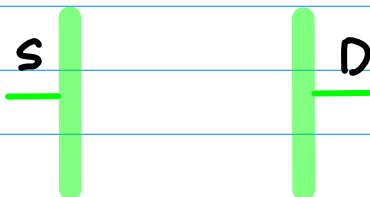
$$0 < V_{GB} < V_t$$

$$V_t < V_{GB}$$

OFF

LIN

SAT



$$V_{GB} < V_t$$

$$V_t < V_{GB}$$

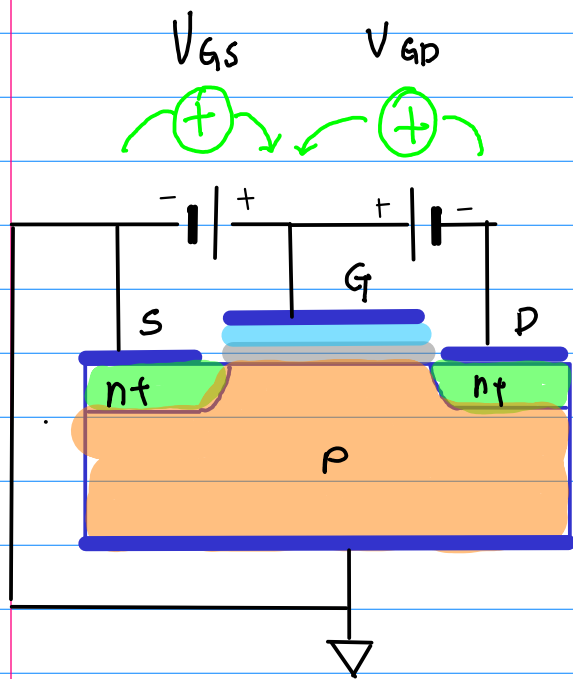
$$V_t < V_{GB}$$

$$V_{DS} < V_{GS} - V_t$$

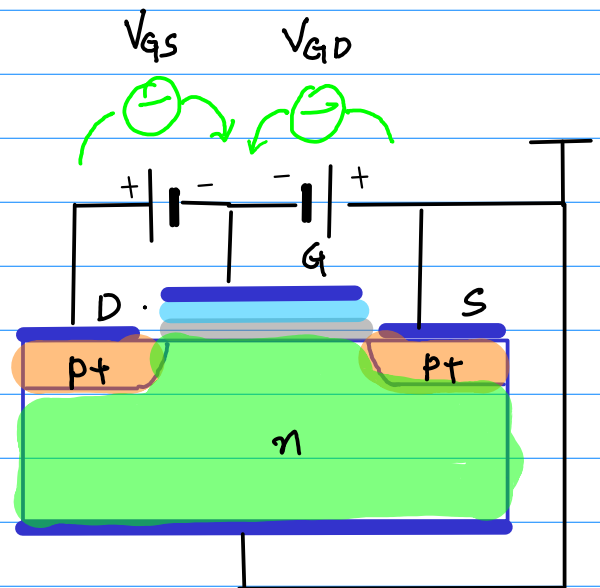
$$V_{DS} > V_{GS} - V_t$$

Accumulation	Depletion	Inversion	
$V_{GB} < 0$	$0 < V_{GB} < V_t$	$V_t < V_{GB}$	
		$V_{DS} < V_{GS} - V_t$	$V_{DS} > V_{GS} - V_t$
OFF		LIN	SAT

Linear Mode Bias Condition (1)



$$V_{GS} > V_{Tn}, \quad V_{GD} > V_{Tn}$$



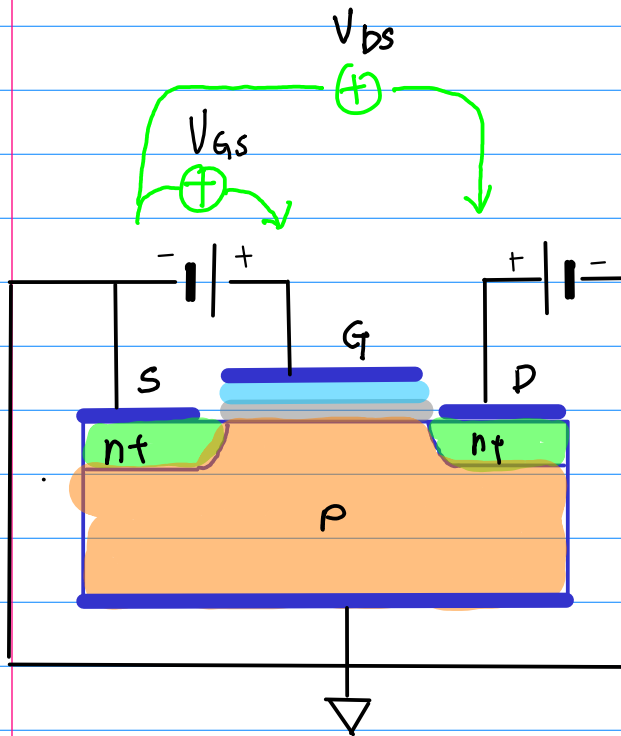
$$V_{GS} < V_{Tp}, \quad V_{GD} < V_{Tp}$$

$$-V_{SG} < V_{Tp}, \quad -V_{DG} < V_{Tp}$$

$$V_{SG} > -V_{Tp}, \quad V_{DG} > -V_{Tp}$$

$$V_{SG} > |V_{Tp}|, \quad V_{DG} > |V_{Tp}|$$

Linear Mode Bias Condition (2)

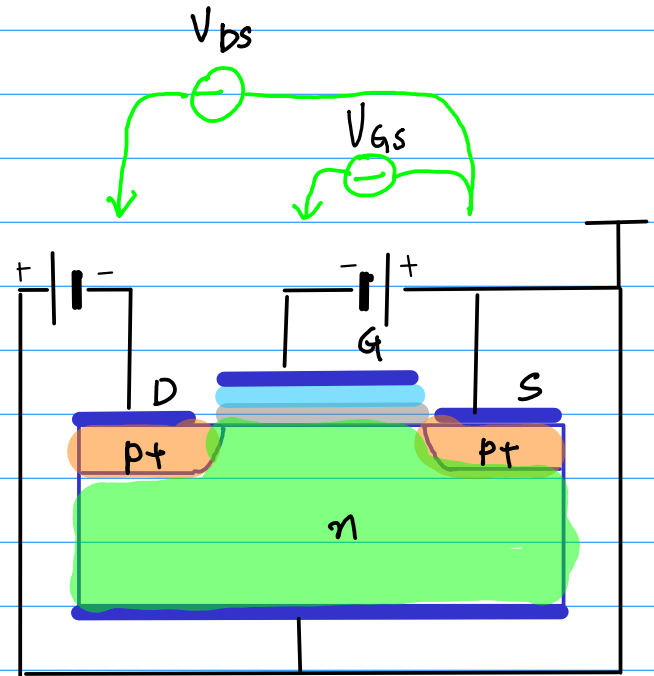


$$V_{GD} = V_{GS} - V_{DS} > V_{Tn}$$

$$V_{GS} - V_{Tn} > V_{DS}$$

$$V_{GS} > V_{Tn},$$

$$V_{DS} < V_{GS} - V_{Tn}$$



$$V_{GD} = V_{GS} - V_{DS} < V_{Tp}$$

$$V_{GS} - V_{Tp} < V_{DS}$$

$$V_{GS} < V_{Tp},$$

$$V_{DS} > V_{GS} - V_{Tp}$$

$$-V_{SD} > -V_{SG} - V_{Tp}$$

$$V_{SD} < V_{SG} + V_{Tp}$$

$$V_{GS} < V_{Tp},$$

$$V_{SD} < V_{SG} + V_{Tp}$$

$$V_{SG} > |V_{Tp}|$$

$$V_{SD} < V_{SG} - |V_{Tp}|$$

Wafer Growth

Photo-lithography

Doping

- Diffusion

- Implantation

Oxidation

Deposition

- Dielectric

- Polysilicon

- Metals

Etching

- Chemical

- Chemical-Mechanical

- Mechanical

Expitaxial Growth

References

Some Figures from the following sites

[1] <http://pages.hmc.edu/harris/cmosvlsi/4e/index.html>
Weste & Harris Book Site

[2] en.wikipedia.org

